# Ultra High Dynamic Range, Shutdown Monolithic Amplifier

 $50\Omega$  30MHz to 2 GHz

# **The Big Deal**

- Ultra-High IP3, +36.4 dBm typ.
- Low supply voltage, 3 to 5V
- Excellent Noise Figure, 1.2 dB typ.
- Shutdown feature

# **Product Overview**

TSS-23LN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-23LN+ has good input and output return loss over a broad frequency range. TSS-23LN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

Feature	Advantages
Broad Band: 30MHz to 2GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular
Extremely High IP3 39.8 dBm typical at 30 MHz 36.4 dBm typical at 1GHz	The TSS-23LN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 11-17 dB above the P1dB point. This feature makes this amplifier ideal for use in: • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers
Shutdown feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage to minimize DC power consumption
Low Noise Figure 1.2 dB at 1 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range
Low Supply Voltage	TSS-23LN+ supports low supply voltage operation which indicate low power consumption.

# **Key Features**



CASE STYLE: DQ1225



# Ultra High Dynamic Range, Shutdown Monolithic Amplifier

## **Product Features**

- High IP3, 36.4 dBm typ. at 1GHz
- Gain, 21.5 dB typ. at 1 GHz
- Low noise figure, 1.2 dB at 1 GHz
- Low voltage, 5V and 3V
- Shutdown feature

### **Typical Applications**

- Base station infrastructure
- CATV
- Cellular

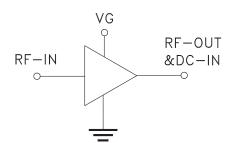


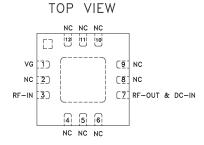
+RoHS Compliant The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

# **General Description**

TSS-23LN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-23LN+ has good input and output return loss over a broad frequency range. TSS-23LN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

### simplified schematic and pad description





Function	Pin Number	Description
RF IN	3	RF Input
RF-OUT and DC-IN	7	RF Output and DC Bias
GND	Paddle	Connections to ground.
NC	2, 4-6, 8-12	No connection, grounded externally
VG	1	Control voltage for shutdown (VG)



# Electrical Specifications<sup>1</sup> at 25°C, & 50 $\Omega$ , unless noted

Parameter	Condition Amplifier (MHz)			N Amplifier- OFF		Amplifier- ON	Amplifier- OFF	Units
		VDD = 5V			VDD = 5V	VDD = 3V	VDD = 3V	
		Min.	Тур.	Max.	Тур.	Тур.	Тур.	
Frequency Range		30		2000	30-2000	30-2000	30-2000	MHz
	30		1.2			1.1		dB
	500		1.2			1.2		
Noise Figure	1000		1.2			1.2		
	1500		1.3			1.4		
	2000		1.4			1.5		
	30	20.7	23.1	25.3	-21	22.4	-21	dB
	500	—	22.2	—	-21	21.4	-21	
Gain	1000	19.2	21.5	23.4	-23	20.2	-24	
	1500	—	20.7	_	-26	19.1	-26	
	2000	17.6	19.9	21.6	-28	18	-27	
Reversed Isolation	30-2000		27		26	27	25	dB
	30		12		12	12	12	dB
	500		12		12	11	12	
Input Return Loss	1000		10		12	8	12	
	1500		10		15	8	15	
	2000		11		19	8	19	
	30		15		2	17	2	dB
	500		15		2	19	2	
Output Return Loss	1000		16		2	18	2	
	1500		12		2	11	2	
	2000		10		2	9	2	
	30		22.8			17.1		dBm
	500		23.8			18.9		
Output Power @1dB compression AMP-ON	1000		24.1			19		
	1500		23.5			18.8		
	2000		22.8			18.1		
	30	—	39.8			34.1		dBm
	500	—	38.0			33.7		
Output IP3 (Pout = 0dBm/Tone)	1000	—	36.4			31.8		
	1500	33	35.5			31.1		
	2000	—	34.0			30.3		
Device Operating Voltage (VDD)		4.75	5	5.25	5	3	3	V
Device Operating Current (ID)			139	163	5	74	3	mA
Control Voltage (VG)			0		5	0	5	V
DC Current (ID) Variation Vs. Temperature <sup>2</sup>			-13			27		uA/degC
DC Current (ID) Variation Vs. Voltage			0.034			0.033		mA/mV
Thermal Resistance			23.3			23.3		degC/W

1. Measured on Mini-Circuits Characterization test board TB-TSS-23LN+. See Characterization Test Circuit (Fig. 1) 2. (Current at 105°C — Current at -45°C)/150

# Absolute Maximum Ratings<sup>3</sup>

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to 105°C		
Storage Temperature	-65°C to 150°C		
Total Power Dissipation	3.3W		
Input Power	28 dBm (5 minutes max.) 10 dBm (continuos) for 0.03-1 GHz 13 dBm (continuos) for 1-2 GHz GHz		
DC Voltage V <sub>DD</sub> <sup>4</sup> (Pad 7)	10V		
DC Voltage V <sub>G</sub> <sup>5</sup> (Pad 1)	10V		

 $^3$  Permanent damage may occur if these limits are exceeded.  $^4$  Measured by keeping V\_{a=0V}  $^5$  Measured by keeping V\_{ba=5V}.

#### Control Voltage (V<sub>G</sub>) Fig. 1

•	,	•		
	Min.	Тур.	Max.	Units
Amplifier-ON	—	0	0.7	V
Amplifier-OFF	1.9	5	—	V



#### Switching Specifications

Parameter	5V Typ.	3V Typ.	Units		
Amplifier ON to Chutdown	OFF TIME (50% Control to 10% RF)	FF TIME (50% Control to 10% RF) 4.8			
Amplifier ON to Shutdown	FALL TIME (90 to 10% RF)	7.4	3.6	μs	
Arralifian Oburtelaum ta Obl	ON TIME (50% Control to 90% RF)		144.7	μs	
Amplifier Shutdown to ON	SE TIME (10% to 90% RF) 60.0 24		200.7		
Control Voltage Leakage			311.0	mV	

# **Characterization Test Circuit / Recommended Application Circuit**

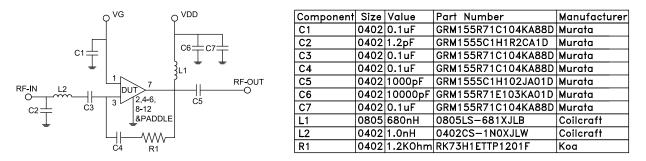
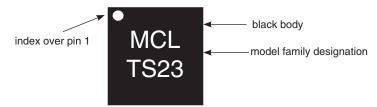


Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-TSS-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

#### Conditions:

- 1. Gain and Return Loss: Pin= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +0dBm/tone at output.
- 3. Switching Time
- RF Signal: Pin=-25 dBm, f<sub>RF</sub>=500 MHz.
- $V_{DD}$ =3 & 5V DC,  $V_G$ =Pulse signal at 1 KHz with  $V_{HIGH}$ =5V,  $V_{LOW}$ =0V, 50% duty cycle.

## **Product Marking**

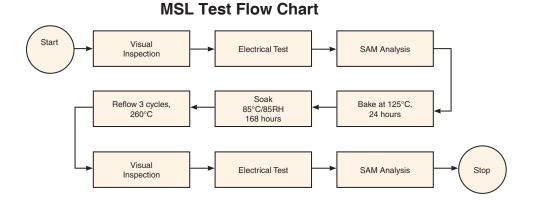


Marking may contain other features or characters for internal lot control

Additional Detailed Technical Information additional information is available on our dash board. To access this information <u>click here</u>				
	Data Table			
Performance Data	Swept Graphs			
	S-Parameter (S2P Files) Data Set (.zip file)			
Case Style	DQ1225 Plastic package, exposed paddle lead finish: Matte-Tin			
Tape & Reel	F66			
Standard quantities available on reel	7" reels with 20, 50, 100, 200, 500 or 1K devices			
Suggested Layout for PCB Design	PL-619			
Evaluation Board	TB-TSS-23LN+			
Environmental Ratings	ENV08T9			

## **ESD** Rating

Human Body Model (HBM): Class 1A (Pass 250 V) in accordance with ANSI/ESD STM 5.1 - 2001



#### **Additional Notes**

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the Standard Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp